Johann P Reithmaier

List of Publications by Year
in descending order

474 papers	11,676 citations	61984 43 h-index	40979 93 g-index
478 all docs	478 docs citations	478 times ranked	7333 citing authors

#	Article	IF	Citations
1	Strong coupling in a single quantum dotâ€“semiconductor microcavity system. Nature, 2004, 432, 197-200.	27.8	1,776
2	Fine structure of neutral and charged excitons in self-assembled In(Ga)As/(Al)GaAs quantum dots. Physical Review B, 2002, 65, .	3.2	933
3	Introduction to the Special Issue on Semiconductor Lasers. IEEE Journal of Selected Topics in Quantum Electronics, 2017, 23, 1-3.	2.9	539
4	Electron and HolegFactors and Exchange Interaction from Studies of the Exciton Fine Structure inIn0.60Ga0.40AsQuantum Dots. Physical Review Letters, 1999, 82, 1748-1751.	7.8	378
5	Optical Modes in Photonic Molecules. Physical Review Letters, 1998, 81, 2582-2585.	7.8	359
6	Long-wavelength InP-based quantum-dash lasers. IEEE Photonics Technology Letters, 2002, 14, 735-737.	2.5	166
7	Control of Vertically CoupledInGaAs/GaAsQuantum Dots with Electric Fields. Physical Review Letters, 2005, 94, 157401.	7.8	138
8	InP based lasers and optical amplifiers with wire-/dot-like active regions. Journal Physics D: Applied Physics, 2005, 38, 2088-2102.	2.8	134
9	Size Dependence of Confined Optical Modes in Photonic Quantum Dots. Physical Review Letters, 1997, 78, 378-381.	7.8	128
10	Tunable photonic crystals fabricated in III-V semiconductor slab waveguides using infiltrated liquid crystals. Applied Physics Letters, 2003, 82, 2767-2769.	3.3	128
11	Zeeman splitting of excitons and biexcitons in singleIn0.60Ga0.40As/GaAsself-assembled quantum dots. Physical Review B, 1998, 58, R7508-R7511.	3.2	121
12	Weak and strong coupling of photons and excitons in photonic dots. Physical Review B, 1998, 57, 9950-9956.	3.2	112
13	Telecom-wavelength (1.5â€‰<i>Î¼</i>m) single-photon emission from InP-based quantum dots. Applied Physics Letters, 2013, 103, .	3.3	111
14	Transient electromagnetically induced transparency in self-assembled quantum dots. Applied Physics Letters, 2008, 92, .	3.3	93
15	Highly efficient GaInAs/(Al)GaAs quantum-dot lasers based on a single active layer versus 980 nm high-power quantum-well lasers. Applied Physics Letters, 2000, 77, 1419-1421.	3.3	92
16	Lasing in high-Q quantum-dot micropillar cavities. Applied Physics Letters, 2006, 89, 051107.	3.3	92
17	Optical Demonstration of a Crystal Band Structure Formation. Physical Review Letters, 1999, 83, 5374-5377.	7.8	91
18	Band offset in elastically strained InGaAs/GaAs multiple quantum wells determined by optical absorption and electronic Raman scattering. Applied Physics Letters, 1990, 56, 536-538.	3.3	89

#	Article	IF	Citations
19	On the nature of quantum dash structures. Journal of Applied Physics, 2004, 95, 6103-6111.	2.5	87
20	High-performance GaInAs/GaAs quantum-dot lasers based on a single active layer. Applied Physics Letters, 1999, 74, 2915-2917.	3.3	86
21	Correlation between the gain profile and the temperature-induced shift in wavelength of quantum-dot lasers. Applied Physics Letters, 2002, 81, 217-219.	3.3	86
22	Size control of InAs quantum dashes. Applied Physics Letters, 2005, 86, 253112.	3.3	84
23	Er doped nanocrystalline ZnO planar waveguide structures for 1.55 Î¼m amplifier applications. Applied Physics Letters, 1999, 75, 2005-2007.	3.3	83
24	Low-threshold high-quantum-efficiency laterally gain-coupled InGaAs/AlGaAs distributed feedback lasers. Applied Physics Letters, 1999, 74, 483-485.	3.3	82
25	Line narrowing in single semiconductor quantum dots: Toward the control of environment effects. Physical Review B, 2002, 66, .	3.2	78
26	Semiconductor quantum dot microcavity pillars with high-quality factors and enlarged dot dimensions. Applied Physics Letters, 2005, 86, 111105.	3.3	78
27	Broad-band wavelength conversion based on cross-gain modulation and four-wave mixing in InAs-InP quantum-dash semiconductor optical amplifiers operating at 1550 nm. IEEE Photonics Technology Letters, 2003, 15, 563-565.	2.5	77
28	InAs/InP Quantum-Dash Lasers and Amplifiers. Proceedings of the IEEE, 2007, 95, 1779-1790.	21.3	76
29	Epitaxial growth of 1.55Î¼m emitting InAs quantum dashes on InP-based heterostructures by GS-MBE for long-wavelength laser applications. Journal of Crystal Growth, 2003, 251, 248-252.	1.5	64
30	High-temperature operating 1.3-Î¼m quantum-dot lasers for telecommunication applications. IEEE Photonics Technology Letters, 2001, 13, 764-766.	2.5	59
31	Strong excitonâ€"photon coupling in semiconductor quantum dot systems. Semiconductor Science and Technology, 2008, 23, 123001.	2.0	59
32	Optical properties ofGa0.8In0.2As/GaAs surface quantum wells. Physical Review B, 1993, 48, 14741-14744.	3.2	58
33	High gain 1.55â€‚Î¼m diode lasers based on InAs quantum dot like active regions. Applied Physics Letters, 2011, 98, .	3.3	58
34	The role of auger recombination in inas 1.3-Î¼m quantum-dot lasers investigated using high hydrostatic pressure. IEEE Journal of Selected Topics in Quantum Electronics, 2003, 9, 1300-1307.	2.9	57
35	Lateral coupling â€" a material independent way to complex coupled DFB lasers. Optical Materials, 2001, 17, 19-25.	3.6	52
36	Investigation of the critical layer thickness in elastically strained InGaAs/GaAlAs quantum wells by photoluminescence and transmission electron microscopy. Applied Physics Letters, 1989, 54, 48-50.	3.3	51

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37	Polariton-polariton scattering in semiconductor microcavities: Experimental observation of thresholdlike density dependence. Physical Review B, 2000, 61, R2409-R2412.	3.2	51
38	Influence of the strain on the formation of GaInAs/GaAs quantum structures. Journal of Crystal Growth, 2006, 286, 6-10.	1.5	49
39	Edge-emitting GaInAs-AlGaAs microlasers. IEEE Photonics Technology Letters, 1999, 11, 943-945.	2.5	48
40	Influence of the As2/As4 growth modes on the formation of quantum dot-like InAs islands grown on InAlGaAs/InP (100). Applied Physics Letters, 2010, 96, 191903.	3.3	48
41	Enhancement of spontaneous emission rates by three-dimensional photon confinement in Bragg microcavities. Physical Review B, 1997, 56, R4367-R4370.	3.2	47
42	Influence of doping density on electron dynamics in GaAsâˆ•AlGaAs quantum cascade lasers. Journal of Applied Physics, 2006, 99, 103106.	2.5	47
43	Temperature stability of static and dynamic properties of 155 Âµm quantum dot lasers. Optics Express, 2018, 26, 6056.	3.4	47
44	Cell adhesion and growth on ultrananocrystalline diamond and diamond-like carbon films after different surface modifications. Applied Surface Science, 2014, 297, 95-102.	6.1	46
45	Bioproperties of nanocrystalline diamond/amorphous carbon composite films. Diamond and Related Materials, 2007, 16, 735-739.	3.9	45
46	Coherent photonic coupling of semiconductor quantum dots. Optics Letters, 2006, 31, 1738.	3.3	43
47	Single photon emission at 1.55â€‰Î¼m from charged and neutral exciton confined in a single quantum dash. Applied Physics Letters, 2014, 105, 021909.	3.3	43
48	Indium desorption during MBE growth of strained InGaAs layers. Journal of Crystal Growth, 1991, 111, 407-412.	1.5	42
49	High-temperature properties of GaInAs/AlGaAs lasers with improved carrier confinement by short-period superlattice quantum well barriers. Applied Physics Letters, 1998, 73, 2863-2865.	3.3	41
50	Ultrafast gain and index dynamics of quantum dash structures emitting at 1.55Î¼m. Applied Physics Letters, 2006, 89, 081102.	3.3	41
51	Large linewidth reduction in semiconductor lasers based on atom-like gain material. Optica, 2019, 6, 1071.	9.3	41
52	Experimental evidence for the transition from two- to three-dimensional behavior of excitons in quantum-well structures. Physical Review B, 1991, 43, 4933-4938.	3.2	40
53	High-performance 980 nm quantum dot lasers for high-power applications. Electronics Letters, 2001, 37, 353.	1.0	40
54	Multiple wavelength amplification in wide band high power 1550â€…nm quantum dash optical amplifier. Electronics Letters, 2004, 40, 760.	1.0	40

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55	Photoreflectance-probed excited states in InAsâˆ•InGaAlAs quantum dashes grown on InP substrate. Applied Physics Letters, 2006, 89, 031908.	3.3	40
56	Telecom wavelength single quantum dots with very small excitonic fine-structure splitting. Applied Physics Letters, 2018, 112, .	3.3	40
57	Gain and noise saturation of wide-band InAs-InP quantum dash optical amplifiers: model and experiments. IEEE Journal of Selected Topics in Quantum Electronics, 2005, 11, 1015-1026.	2.9	38
58	Tribological properties of ultrananocrystalline diamond films in various test atmosphere. Tribology International, 2011, 44, 2042-2049.	5.9	38
59	High-density 1.54 Î¼m InAs/InGaAlAs/InP(100) based quantum dots with reduced size inhomogeneity. Journal of Crystal Growth, 2015, 425, 299-302.	1.5	38
60	Single-photon emission of InAs/InP quantum dashes at 1.55â€‰<i>Î¼</i>m and temperatures up to 80â€‰K. Applied Physics Letters, 2016, 108, .	3.3	38
61	Strong variation of the excitongfactors in self-assembledIn0.60Ga0.40Asquantum dots. Physical Review B, 1999, 60, R8481-R8484.	3.2	37
62	InAsâˆ•InP 1550â€…nm quantum dash semiconductor optical amplifiers. Electronics Letters, 2002, 38, 1350.	1.0	37
63	Radiative emission dynamics of quantum dots in a single cavity micropillar. Physical Review B, 2006, 74, .	3.2	37
64	Focused ion-beam implantation induced thermal quantum-well intermixing for monolithic optoelectronic device integration. IEEE Journal of Selected Topics in Quantum Electronics, 1998, 4, 595-605.	2.9	36
65	Optical gain properties of InAsâˆ•InAlGaAsâˆ•InP quantum dash structures with a spectral gain bandwidth of more than 300nm. Applied Physics Letters, 2006, 89, 061107.	3.3	36
66	Highâ€Purity Triggered Singleâ€Photon Emission from Symmetric Single InAs/InP Quantum Dots around the Telecom Câ€Band Window. Advanced Quantum Technologies, 2020, 3, 1900082.	3.9	35
67	Optical spectroscopy of single InAs/InGaAs quantum dots in a quantum well. Applied Physics Letters, 2002, 81, 4898-4900.	3.3	34
68	Exciton-photon coupling in photonic wires. Physical Review B, 1998, 57, R6807-R6810.	3.2	33
69	Rabi oscillations and self-induced transparency in InAs/InP quantum dot semiconductor optical amplifier operating at room temperature. Optics Express, 2013, 21, 26786.	3.4	33
70	Exciton and biexciton dynamics in single self-assembled InAs/InGaAlAs/InP quantum dash emitting near 1.55â€‰<i>Î¼</i>m. Applied Physics Letters, 2013, 103, .	3.3	33
71	High Speed 1.55 Î¼m InAs/InGaAlAs/InP Quantum Dot Lasers. IEEE Photonics Technology Letters, 2014, 26, 11-13.	2.5	33
72	Magneto-optical investigations of single self-assembled InAs/InGaAlAs quantum dashes. Applied Physics Letters, 2003, 82, 2799-2801.	3.3	32

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73	Cross-gain modulation in inhomogeneously broadened gain spectra of InP-Based 1550 nm quantum dash optical amplifiers: Small-signal bandwidth dependence on wavelength detuning. Applied Physics Letters, 2003, 82, 4660-4662.	3.3	32
74	Temperature-Insensitive High-Speed Directly Modulated 1.55-<inline-formula> <tex-math notation="LaTeX">$mu ext{m}$ </tex-math> </inline-formula> Quantum Dot Lasers. IEEE Photonics Technology Letters, 2016, 28, 2451-2454.	2.5	32
75	Laser emission from photonic dots. Applied Physics Letters, 1997, 71, 488-490.	3.3	31
76	Enhanced direct-modulated bandwidth of 37â€…GHz by a multi-section laser with a coupled-cavity-injection-grating design. Electronics Letters, 2003, 39, 1592.	1.0	31
77	High frequency characteristics of InAs/GaInAs quantum dot distributed feedback lasers emitting at 1.3 [micro sign]m. Electronics Letters, 2001, 37, 1223.	1.0	30
78	Photoreflectance spectroscopy of vertically coupled InGaAs/GaAs double quantum dots. Solid State Communications, 2001, 117, 401-406.	1.9	30
79	High-power quantum dot lasers with improved temperature stability of emission wavelength for uncooled pump sources. Electronics Letters, 2005, 41, 1125.	1.0	30
80	High-Speed Low-Noise InAs/InAlGaAs/InP 1.55-$mu{m m}$ Quantum-Dot Lasers. IEEE Photonics Technology Letters, 2012, 24, 809-811.	2.5	30
81	Optically probed wetting layer in InAs/InGaAlAs/InP quantum-dash structures. Applied Physics Letters, 2005, 86, 101904.	3.3	29
82	Wettability and protein adsorption on ultrananocrystalline diamond/amorphous carbon composite films. Diamond and Related Materials, 2009, 18, 895-898.	3.9	29
83	Heterodyne pump probe measurements of nonlinear dynamics in an indium phosphide photonic crystal cavity. Applied Physics Letters, 2013, 103, .	3.3	29
84	High-power 980â€…nm quantum dot broad area lasers. Electronics Letters, 2003, 39, 1655.	1.0	28
85	Electronic structure, morphology and emission polarization of enhanced symmetry InAs quantum-dot-like structures grown on InP substrates by molecular beam epitaxy. Journal of Applied Physics, 2013, 114, .	2.5	28
86	Exciton lifetime and emission polarization dispersion in strongly in-plane asymmetric nanostructures. Physical Review B, 2017, 96, .	3.2	28
87	Dynamics of carrier-capture processes inGaxIn1âˆ’xAs/GaAs near-surface quantum wells. Physical Review B, 1995, 51, 4657-4660.	3.2	27
88	Improved performance of MBE grown quantum-dot lasers with asymmetric dots in a well design emitting near 1.3Î¼m. Journal of Crystal Growth, 2003, 251, 742-747.	1.5	27
89	High-gain wavelength-stabilized 1.55 <i>Î¼</i>m InAs/InP(100) based lasers with reduced number of quantum dot active layers. Applied Physics Letters, 2013, 102, .	3.3	27
90	Large anisotropy of electron and hole<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi>g</mml:mi></mml:math>factors in infrared-emitting InAs/InAlGaAs self-assembled quantum dots. Physical Review B, 2016, 93, .	3.2	27

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91	Minimum feature sizes and ion beam profile for a focused ion beam system with post-objective lens retarding and acceleration mode. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1994, 12, 3518.	1.6	26
92	Telecom wavelength emitting single quantum dots coupled to InP-based photonic crystal microcavities. Applied Physics Letters, 2017, 110, .	3.3	26
93	Widely tunable narrow-linewidth 1.5 <i>Î¼</i>m light source based on a monolithically integrated quantum dot laser array. Applied Physics Letters, 2017, 110, .	3.3	26
94	InAs/GaInAs quantum dot DFB lasers emitting at 1.3 [micro sign]m. Electronics Letters, 2001, 37, 634.	1.0	25
95	Wide range tunable laterally coupled distributed-feedback lasers based on InGaAs-GaAs quantum dots. IEEE Photonics Technology Letters, 2002, 14, 1246-1248.	2.5	25
96	High-Power Tunnel-Injection 1060-nm InGaAsâ€"(Al)GaAs Quantum-Dot Lasers. IEEE Photonics Technology Letters, 2009, 21, 999-1001.	2.5	25
97	Influence of electronic coupling on the radiative lifetime in the (In,Ga)As/GaAs quantum dotâ€"quantum well system. Physical Review B, 2012, 85, .	3.2	25
98	Rabi oscillations in a room-temperature quantum dash semiconductor optical amplifier. Physical Review B, 2014, 90, .	3.2	25
99	Importance of Auger recombination in InAs 1.3â€…[micro sign]m quantum dot lasers. Electronics Letters, 2003, 39, 58.	1.0	24
100	Gain, index variation, and linewidth-enhancement factor in 980-nm quantum-well and quantum-dot lasers. IEEE Journal of Quantum Electronics, 2005, 41, 117-126.	1.9	24
101	Plasma amination of ultrananocrystalline diamond/amorphous carbon composite films for the attachment of biomolecules. Diamond and Related Materials, 2011, 20, 254-258.	3.9	24
102	Low temperature growth of nanocrystalline and ultrananocrystalline diamond films: A comparison. Physica Status Solidi (A) Applications and Materials Science, 2012, 209, 1664-1674.	1.8	24
103	All-optical signal processing at 10â€‰GHz using a photonic crystal molecule. Applied Physics Letters, 2013, 103, .	3.3	24
104	Confinement of light hole valenceâ€band states in pseudomorphic InGaAs/Ga(Al)As quantum wells. Applied Physics Letters, 1990, 57, 957-959.	3.3	23
105	22-GHz Modulation Bandwidth of Long Cavity DBR Laser by Using a Weakly Laterally Coupled Grating Fabricated by Focused Ion Beam Lithography. IEEE Photonics Technology Letters, 2004, 16, 18-20.	2.5	23
106	Reduction of the threshold current density of GaAs/AlGaAs quantum cascade lasers by optimized injector doping and growth conditions. Journal of Crystal Growth, 2005, 278, 775-779.	1.5	23
107	Polarization-dependent optical properties of planar photonic crystals infiltrated with liquid crystals. Applied Physics Letters, 2005, 87, 121105.	3.3	23
108	Thermal quenching of photoluminescence from InAsâˆ•In0.53Ga0.23Al0.24Asâˆ•InP quantum dashes with different sizes. Applied Physics Letters, 2006, 89, 151902.	3.3	23

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109	Optical properties of low-strained InxGa1âˆ’xAsâˆ•GaAs quantum dot structures at the two-dimensionalâ€“three-dimensional growth transition. Journal of Applied Physics, 2006, 100, 013503.	2.5	23
110	A nearly instantaneous gain response in quantum dash based optical amplifiers. Applied Physics Letters, 2010, 97, .	3.3	23
111	Low-density InP-based quantum dots emitting around the 1.5â€‰<i>Î¼</i>m telecom wavelength range. Applied Physics Letters, 2014, 104, .	3.3	23
112	Electron and hole<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi>g</mml:mi></mml:math>factors in InAs/InAlGaAs self-assembled quantum dots emitting at telecom wavelengths. Physical Review B, 2015, 92, .	3.2	23
113	Short-cavity edge-emitting lasers with deeply etched distributed Bragg mirrors. Electronics Letters, 1999, 35, 154.	1.0	22
114	Single-mode distributed feedback and microlasers based on quantum-dot gain material. IEEE Journal of Selected Topics in Quantum Electronics, 2002, 8, 1035-1044.	2.9	22
115	Deeply etched two-dimensional photonic crystals fabricated on GaAs/AlGaAs slab waveguides by using chemically assisted ion beam etching. Microelectronic Engineering, 2002, 61-62, 875-880.	2.4	22
116	Static and dynamic properties of laterally coupled DFB lasers based on InAsâˆ•InP QDash structures. Electronics Letters, 2005, 41, 808.	1.0	22
117	Complex (As2S3)(100âˆ’)(AgI) chalcogenide glasses for gas sensors. Sensors and Actuators B: Chemical, 2009, 143, 395-399.	7.8	22
118	Phonon-assisted radiative recombination of excitons confined in strongly anisotropic nanostructures. Physical Review B, 2014, 90, .	3.2	22
119	Incorporation and study of SiV centers in diamond nanopillars. Diamond and Related Materials, 2016, 64, 64-69.	3.9	22
120	Patterning of the surface termination of ultrananocrystalline diamond films for guided cell attachment and growth. Surface and Coatings Technology, 2017, 321, 229-235.	4.8	22
121	Gallium desorption during growth of (Al,Ga)As by molecular beam epitaxy. Applied Physics Letters, 1992, 61, 1222-1224.	3.3	21
122	Photonic defect states in chains of coupled microresonators. Physical Review B, 2001, 64, .	3.2	21
123	Recent advances in semiconductor quantum-dot lasers. Comptes Rendus Physique, 2003, 4, 611-619.	0.9	21
124	Recombination mechanisms in InAs/InP quantum dash lasers studied using high hydrostatic pressure. Physica Status Solidi (B): Basic Research, 2004, 241, 3427-3431.	1.5	21
125	Photoreflectance determination of the wetting layer thickness in the InxGa1âˆ’xAsâˆ•GaAs quantum dot system for a broad indium content range of 0.3â€“1. Journal of Applied Physics, 2006, 100, 103529.	2.5	21
126	Magnetic field control of the neutral and charged exciton fine structure in single quantum dashes emitting at 1.55â€‰Î¼m. Applied Physics Letters, 2015, 106, 053114.	3.3	21

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127	InP-based single-photon sources operating at telecom C-band with increased extraction efficiency. Applied Physics Letters, 2021, 118, .	3.3	21
128	First order gainâ€coupled GaInAs/GaAs distributed feedback laser diodes patterned by focused ion beam implantation. Applied Physics Letters, 1996, 69, 1906-1908.	3.3	20
129	High-frequency properties of 1.55 Î¼m laterally complex coupled distributed feedback lasers fabricated by focused-ion-beam lithography. Applied Physics Letters, 2000, 77, 325-327.	3.3	20
130	High Performance 1.3 Âµm Quantum-Dot Lasers. Japanese Journal of Applied Physics, 2002, 41, 1158-1161.	1.5	20
131	InP-based quantum dash lasers for wide gain bandwidth applications. Journal of Crystal Growth, 2005, 278, 346-350.	1.5	20
132	On the development of the morphology of ultrananocrystalline diamond films. Physica Status Solidi (A) Applications and Materials Science, 2011, 208, 70-80.	1.8	20
133	Coherent control in a semiconductor optical amplifier operating at room temperature. Nature Communications, 2014, 5, 5025.	12.8	20
134	Deterministic Arrays of Epitaxially Grown Diamond Nanopyramid<i>s</i> with Embedded Siliconâ€Vacancy Centers. Advanced Optical Materials, 2019, 7, 1800715.	7.3	20
135	InGaAs/AlGaAs quantum dot DFB lasers operating up to 213Â°C. Electronics Letters, 1999, 35, 2036.	1.0	20
136	Highly Resolved Maskless Patterning on InP by Focused Ion Beam Enhanced Wet Chemical Etching. Japanese Journal of Applied Physics, 1999, 38, 6142-6144.	1.5	19
137	1.55 Î¼m single mode lasers with complex coupled distributed feedback gratings fabricated by focused ion beam implantation. Applied Physics Letters, 1999, 75, 1491-1493.	3.3	19
138	Near-field mapping of the electromagnetic field in confined photon geometries. Physical Review B, 2002, 66, .	3.2	19
139	High brightness GaInAs/(Al)GaAs quantum-dot tapered lasers at 980 nm with high wavelength stability. Applied Physics Letters, 2004, 84, 2238-2240.	3.3	19
140	Time-resolved chirp in an InAsâˆ•InP quantum-dash optical amplifier operating with 10Gbitâˆ•s data. Applied Physics Letters, 2005, 87, 021104.	3.3	19
141	GaInAs/(Al)GaAs quantum-dot lasers with high wavelength stability. Semiconductor Science and Technology, 2008, 23, 085022.	2.0	19
142	Tribological properties of nanocrystalline diamond films deposited by hot filament chemical vapor deposition. AIP Advances, 2012, 2, .	1.3	19
143	50 mW CW-operated single-mode surface-emitting AlGaAs lasers with 45 degrees total reflection mirrors. IEEE Photonics Technology Letters, 1992, 4, 698-700.	2.5	18
144	Nanocrystalline diamond/amorphous carbon composite coatings for biomedical applications. Diamond and Related Materials, 2008, 17, 882-887.	3.9	18

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145	Investigation of the UV/O₃ treatment of ultrananocrystalline diamond films. Surface and Interface Analysis, 2010, 42, 1152-1155.	1.8	18
146	Electrical properties of ultrananocrystalline diamond/amorphous carbon nanocomposite films. Diamond and Related Materials, 2010, 19, 449-452.	3.9	18
147	Excitonic fine structure and binding energies of excitonic complexes in single InAs quantum dashes. Physical Review B, 2016, 94, .	3.2	18
148	12 [micro sign]m long edge-emitting quantum-dot laser. Electronics Letters, 2001, 37, 690.	1.0	17
149	On the tunnel injection of excitons and free carriers from In0.53Ga0.47Asâˆ•In0.53Ga0.23Al0.24As quantum well to InAsâˆ•In0.53Ga0.23Al0.24As quantum dashes. Applied Physics Letters, 2006, 89, 061902.	3.3	17
150	Widely tunable single-mode quantum cascade lasers with two monolithically coupled Fabry-PÃ©rot cavities. Applied Physics Letters, 2006, 89, 241126.	3.3	17
151	Cross talk free multi channel processing of 10 Gbit/s data via four wave mixing in a 1550 nm InAs/InP quantum dash amplifier. Optics Express, 2008, 16, 19072.	3.4	17
152	Nanocrystalline diamond containing hydrogels and coatings for acceleration of osteogenesis. Diamond and Related Materials, 2011, 20, 165-169.	3.9	17
153	Height-driven linear polarization of the surface emission from quantum dashes. Semiconductor Science and Technology, 2012, 27, 105022.	2.0	17
154	Highâ€power singleâ€mode AlGaAs lasers with bentâ€waveguide nonabsorbing etched mirrors. Journal of Applied Physics, 1992, 72, 2131-2135.	2.5	16
155	Transform-limited picosecond optical pulses from a mode-locked InGaAs/AlGaAs QW laser with integrated passive waveguide cavity and QW modulator. IEEE Photonics Technology Letters, 1993, 5, 896-899.	2.5	16
156	First order gain and index coupled distributed feedback lasers in ZnSeâ€based structures with finely tunable emission wavelengths. Applied Physics Letters, 1996, 68, 599-601.	3.3	16
157	Enhanced exciton-phonon scattering inInxGa1âˆ’xAs/GaAsquantum wires. Physical Review B, 1997, 56, 12096-12099.	3.2	16
158	GaAsâˆ•AlGaAs quantum cascade micro lasers based on monolithic semiconductor-air Bragg mirrors. Electronics Letters, 2004, 40, 120.	1.0	16
159	Spectrally resolved dynamics of inhomogeneously broadened gain in InAsâˆ•InP1550nm quantum-dash lasers. Applied Physics Letters, 2004, 85, 5505-5507.	3.3	16
160	Device performance and wavelength tuning behavior of ultra-short quantum-cascade microlasers with deeply etched Bragg-mirrors. IEEE Journal of Selected Topics in Quantum Electronics, 2005, 11, 1048-1054.	2.9	16
161	Modulation speed enhancement by coupling to higher order resonances: a road towards 40 GHz bandwidth lasers on InP. , 0, , .		16
162	Dependence of saturation effects on electron confinement and injector doping in GaAsâˆ•Al0.45Ga0.55As quantum-cascade lasers. Applied Physics Letters, 2006, 88, 251109.	3.3	16

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163	Microthermography of diode lasers: The impact of light propagation on image formation. Journal of Applied Physics, 2009, 105, 014502.	2.5	16
164	Characterization of pulsed laser deposited chalcogenide thin layers. Applied Surface Science, 2009, 255, 5318-5321.	6.1	16
165	Influence of the surface termination of ultrananocrystalline diamond/amorphous carbon composite films on their interaction with neurons. Diamond and Related Materials, 2012, 26, 60-65.	3.9	16
166	Nonlinear pulse propagation in InAs/InP quantum dot optical amplifiers: Rabi oscillations in the presence of nonresonant nonlinearities. Physical Review B, 2015, 91, .	3.2	16
167	Interface structure and strain state of InAs nano-clusters embedded in silicon. Acta Materialia, 2015, 90, 133-139.	7.9	16
168	Static and dynamic characteristics of an InAs/InP quantum-dot optical amplifier operating at high temperatures. Optics Express, 2017, 25, 27262.	3.4	16
169	Novel Ultra Localized and Dense Nitrogen Delta-Doping in Diamond for Advanced Quantum Sensing. Nano Letters, 2020, 20, 3192-3198.	9.1	16
170	Focused ion beam implantation for opto- and microelectronic devices. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1998, 16, 2562.	1.6	15
171	Laterally coupled DBR laser emitting at 1.55 Î¼m fabricated by focused ion beam lithography. IEEE Photonics Technology Letters, 2002, 14, 1037-1039.	2.5	15
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